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N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$V_{DS}(V)$ $R_{DS(on)}(\Omega)$ $I_{D}(On)$				
100	0.€Ĝ at V _{GS} = 10 V	1F			
	0.1I €at V _{GS} = HË V	1Đ			

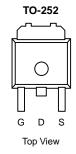
FEATURES

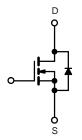
- TrenchFET® Power MOSFETS
- 175 °C Junction Temperature
- 100 % R_g Tested



APPLICATIONS

· Primary Side Switch





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	100			
Gate-Source Voltage	V_{GS}	± 20	V		
Continuous Danis Comment /T 475 90\b	T _C = 25 °C		1F		
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 125 °C	- I _D	Î.F		
Pulsed Drain Current	I _{DM}	4F	Α		
Continuous Source Current (Diode Conduction)	I _S	1F			
Avalanche Current	I _{AR}	1Đ			
Repetitive Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AR}	1Ð.€	mJ	
Maximum Power Dissipation	T _C = 25 °C	P _D	6Đ ^b	W	
Maximum Fower Dissipation	T _A = 25 °C	. 0	2.I ^a		
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
hungtion to Ambienti	t ≤ 10 s	- R _{thJA}	1Î	2G	°C/W	
Junction-to-Ambient ^a	Steady State		4ĺ	5Ϊ		
Junction-to-Case		R _{thJC}	2	2.4		

Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. See SOA curve for voltage derating.



Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static					l l		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2		4	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = 100 V, V _{GS} = 0 V			1	1	
Zero Gate Voltage Drain Current	I_{DSS}	V _{DS} = 100 V, V _{GS} = 0 V, T _J = 125 °C			50	μΑ	
		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 175 °C			250	1	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	15			Α	
		V _{GS} = 10 V, I _D = 6 A		0.137 0.149			
Davis Course Co Otata Basista ash	P	V _{GS} = 10 V, I _D = 6 A, T _J = 125 °C		0.190	0.209	Ω	
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 6A, T _J = 175 °C		0.250	0.276		
		V _{GS} = 4.5 V, I _D = 3 A		0.151	0.167		
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 6 A		25		S	
Dynamic ^a							
Input Capacitance	C _{iss}			852		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		106			
Reverse Transfer Capacitance	C _{rss}			70			
Total Gate Charge ^c	Q_g			20	23		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 12 \text{ A}$		5.2		nC	
Gate-Drain Charge ^c	Q_{gd}			7			
Gate Resistance	R _g		1		3.2	Ω	
Turn-On Delay Time ^c	t _{d(on)}			8	12		
Rise Time ^c	t _r	$V_{DD} = 75 \text{ V}, R_L = 5 \Omega$		35	55		
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 12 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 2.5 \Omega$		17	25	ns	
Fall Time ^c	t _f			30	45		
Source-Drain Diode Ratings and Cha	racteristic (T	_C = 25 °C)					
Pulsed Current	I _{SM}				12	Α	
Diode Forward Voltage ^b	V_{SD}	$I_F = 12 \text{ A}, V_{GS} = 0 \text{ V}$		0.9	1.5	V	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 12 A, dI/dt = 100 A/μs		55	85	ns	

Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. Independent of operating temperature.

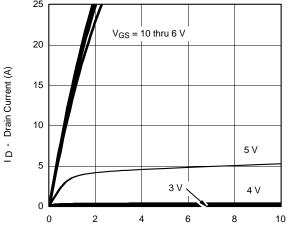
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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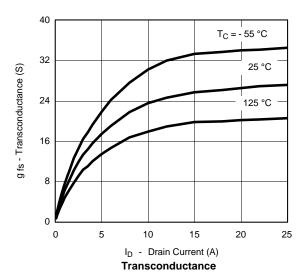
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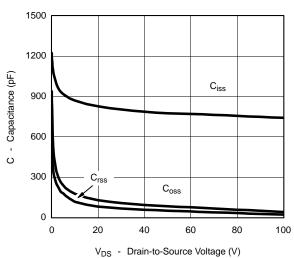
TYPICAL CHARACTERISTICS (25 °C unless noted)



 $V_{\text{DS}}\,$ - Drain-to-Source Voltage (V)

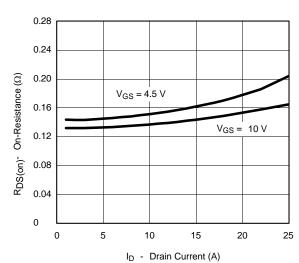
Output Characteristics



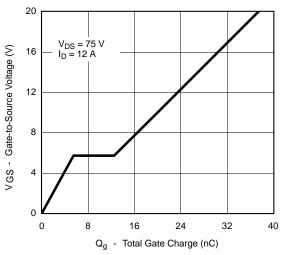


Capacitance

Transfer Characteristics



On-Resistance vs. Drain Current

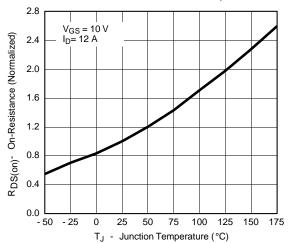


Gate Charge



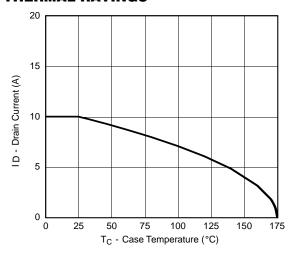
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TYPICAL CHARACTERISTICS (25 °C unless noted)

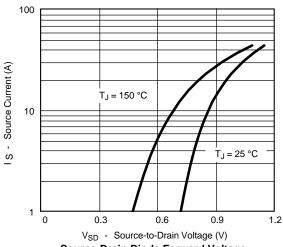


On-Resistance vs. Junction Temperature

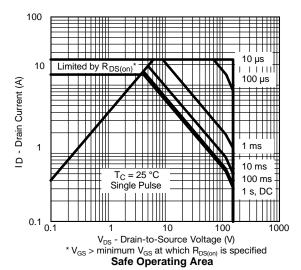
THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature



Source-Drain Diode Forward Voltage

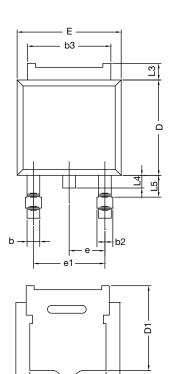


Normalized Thermal Transient Impedance, Junction-to-Case

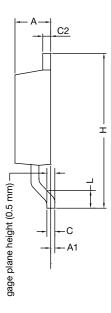




TO-252AA CASE OUTLINE



E1



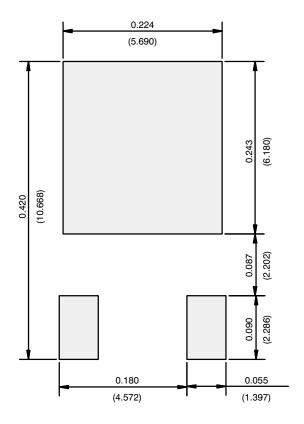
	MILLIMETERS		INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	5.21	-	0.205	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090 BSC		
e1	4.56 BSC		0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	
ECN: X12-0247-Rev. M, 24-Dec-12					

DWG: 5347

Note

• Dimension L3 is for reference only.

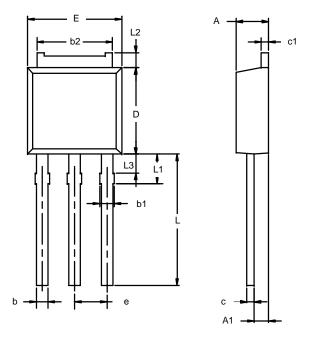
RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)



TO-251AA (DPAK)



Note: Dimension L3 is for reference only.

	MILLIM	IETERS	INC	HES	
Dim	Min	Max	Min	Max	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
b	0.71	0.89	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.43	0.206	0.214	
С	0.46	0.58	0.018	0.023	
с1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
Е	6.48	6.73	0.255	0.265	
е	2.28	BSC	0.090 BSC		
L	8.89	9.53	0.350	0.375	
L1	1.91	2.28	0.075	0.090	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.045	0.060	
ECN: S-03946—Rev. E, 09-Jul-01 DWG: 5346					

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